

General Description

The WSD3095DN56 is the highest performance trench N-ch MOSFET with extreme high cell density, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The WSD3095DN56 meet the RoHS and Green Product requirement 100% EAS guaranteed with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

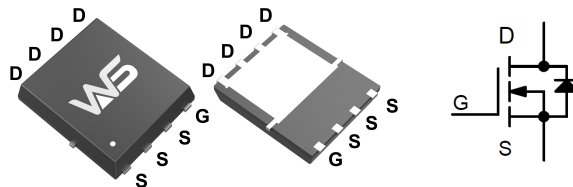
Product Summary

BVDSS	RDSON	ID
30V	3.5mΩ	95A

Applications

- Battery protection
- Load switch
- Uninterruptible power supply

DFN5X6-8 Pin Configuration



Absolute Maximum Ratings (Tc=25°C unless otherwise noted)

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	30	V
V _{GS}	Gate-Source Voltage	±20	V
I _D @T _C =25°C	Continuous Drain Current, V _{GS} @ 10V ₁	90	A
I _D @T _C =100°C	Continuous Drain Current, V _{GS} @ 10V ₁	51	A
I _D @T _A =25°C	Continuous Drain Current, V _{GS} @ 10V ₁	15	A
I _D @T _A =70°C	Continuous Drain Current, V _{GS} @ 10V ₁	12	A
I _{DM}	Pulsed Drain Current ₂	160	A
EAS	Single Pulse Avalanche Energy ₃	115.2	mJ
I _{AS}	Avalanche Current	48	A
P _D @T _C =25°C	Total Power Dissipation ₄	59	W
P _D @T _A =25°C	Total Power Dissipation ₄	2	W
T _{STG}	Storage Temperature Range	-55 to 150	°C
T _J	Operating Junction Temperature Range	-55 to 150	°C
R _{θJA}	Thermal Resistance Junction-Ambient ₁	62	°C/W
R _{θJC}	Thermal Resistance Junction-Case ₁	2.1	°C/W

Electrical Characteristics (T_J=25°C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BVDSS	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	30	---	---	V
ΔBVDSS/ΔT _J	BVDSS Temperature Coefficient	Reference to 25°C, I _D =1mA	---	0.028	---	V/°C
RDS(ON)	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =30A	---	3.5	5.5	mΩ
		V _{GS} =4.5V, I _D =15A	---	6.5	8.5	
VGS(th)	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	1.0	1.6	2.5	V
ΔVGS(th)	Temperature Coefficient		---	-6.16	---	mV/°C
IDSS	Drain-Source Leakage Current	V _{DS} =24V, V _{GS} =0V, T _J =25°C	---	---	1	uA
		V _{DS} =24V, V _{GS} =0V, T _J =55°C	---	---	5	
IGSS	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
gfs	Forward Transconductance	V _{DS} =5V, I _D =30A	---	22	---	S
R _g	Gate Resistance	V _{DS} =0V, V _{GS} =0V, f=1MHz	---	1.7	3.4	Ω
Q _g	Total Gate Charge (4.5V)	V _{DS} =15V, V _{GS} =4.5V, I _D =15A	---	20	---	nC
Q _{gs}	Gate-Source Charge		---	7.6	---	
Q _{gd}	Gate-Drain Charge		---	7.2	---	
Td(on)	Turn-On Delay Time	V _{DD} =15V, V _{GS} =10V, R _G =3.3Ω I _D =15A	---	7.8	---	ns
T _r	Rise Time		---	15	---	
Td(off)	Turn-Off Delay Time		---	37.3	---	
T _f	Fall Time		---	10.6	---	
C _{iss}	Input Capacitance	V _{DS} =15V, V _{GS} =0V, f=1MHz	---	2295	---	pF
C _{oss}	Output Capacitance		---	267	---	
C _{rss}	Reverse Transfer Capacitance		---	210	---	
I _s	Continuous Source Current ^{1,5}	V _G =V _D =0V, Force Current	---	---	80	A
ISM	Pulsed Source Current ^{2,5}		---	---	160	A
VSD	Diode Forward Voltage ²	V _{GS} =0V, I _s =1A, T _J =25°C	---	---	1.2	V
t _{rr}	Reverse Recovery Time	IF=30A, dI/dt=100A/μs, T _J =25°C	---	14	---	nS
Q _{rr}	Reverse Recovery Charge		---	5	---	nC

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width .The EAS data shows Max. rating .
- 3.The test cond ≅ 300us , duty cycle ition is VDD=25≅V,V 2%GS =10V,L=0.1mH,IAS=53.8A
- 4.The power dissipation is limited by 175°C junction temperature
- 5.The data is theoretically the same as ID and IDM , in real applications , should be limited by total power dissipation.

Typical Characteristics

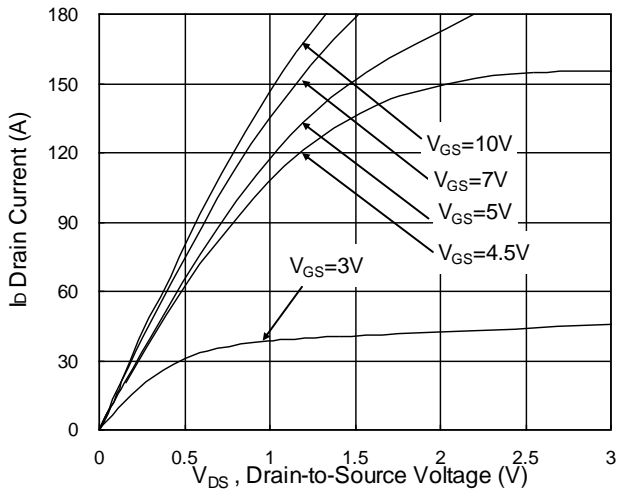


Fig.1 Typical Output Characteristics

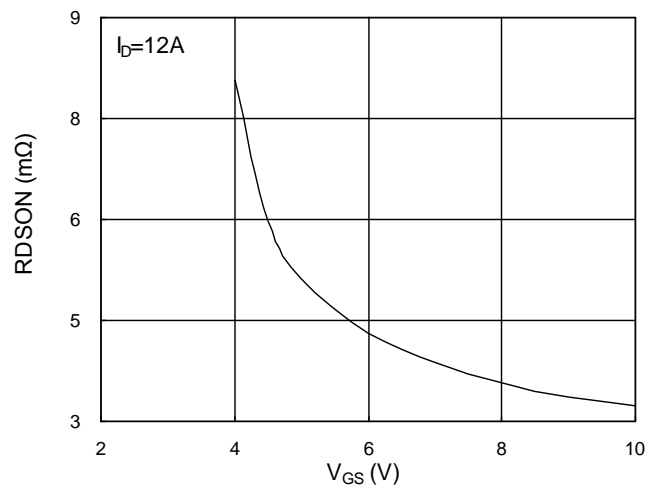


Fig.2 On-Resistance vs. G-S Voltage

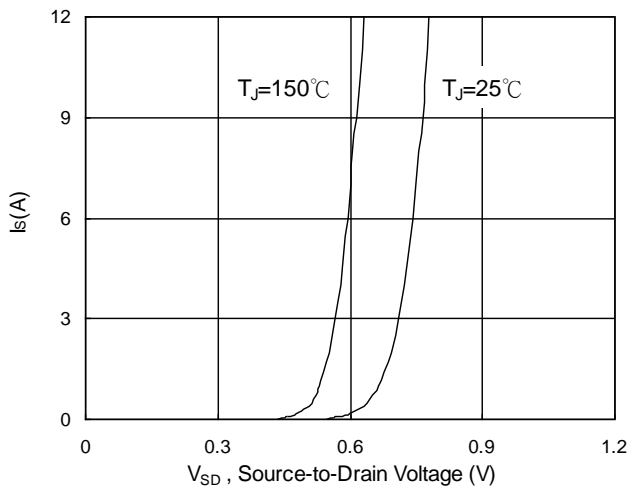


Fig.3 Forward Characteristics of Reverse

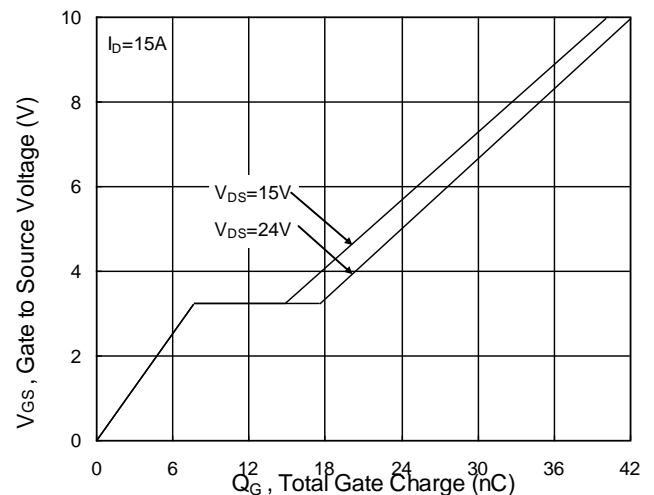


Fig.4 Gate-Charge Characteristics

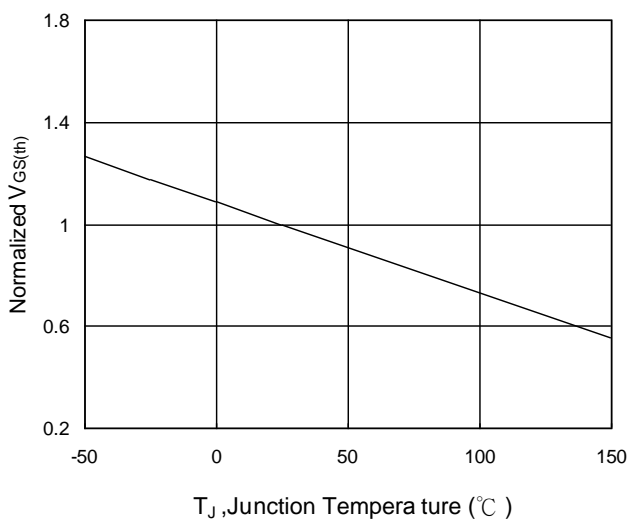


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

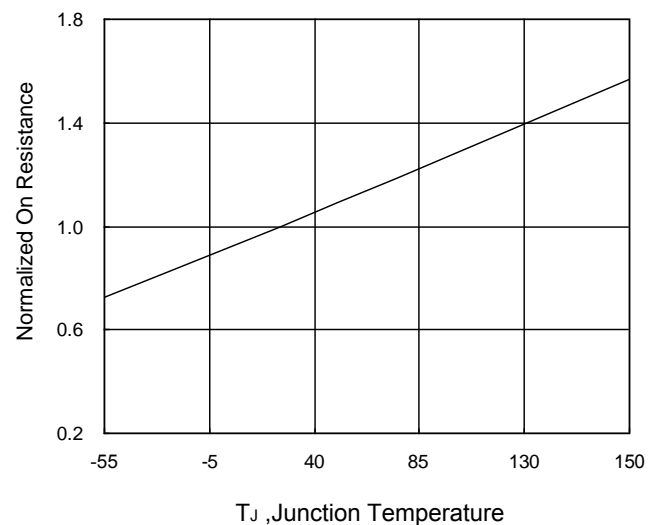


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

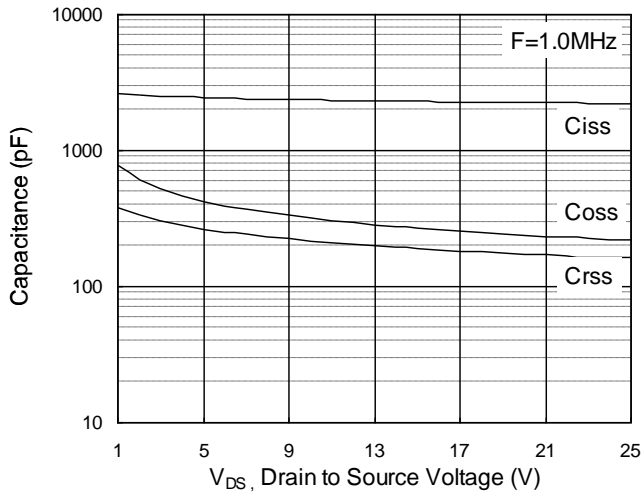


Fig.7 Capacitance

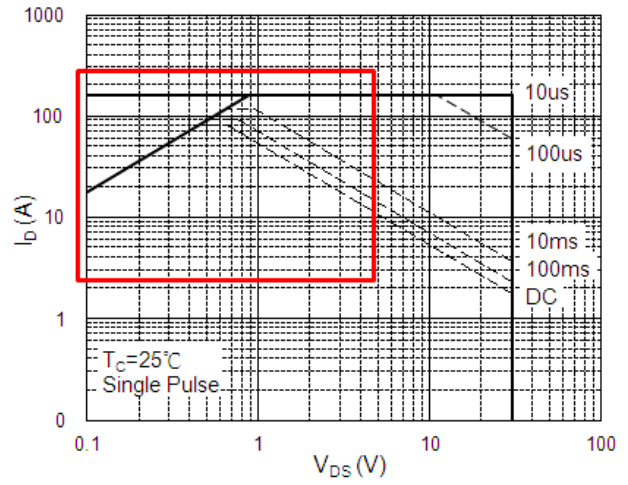


Fig.8 Safe Operating Area

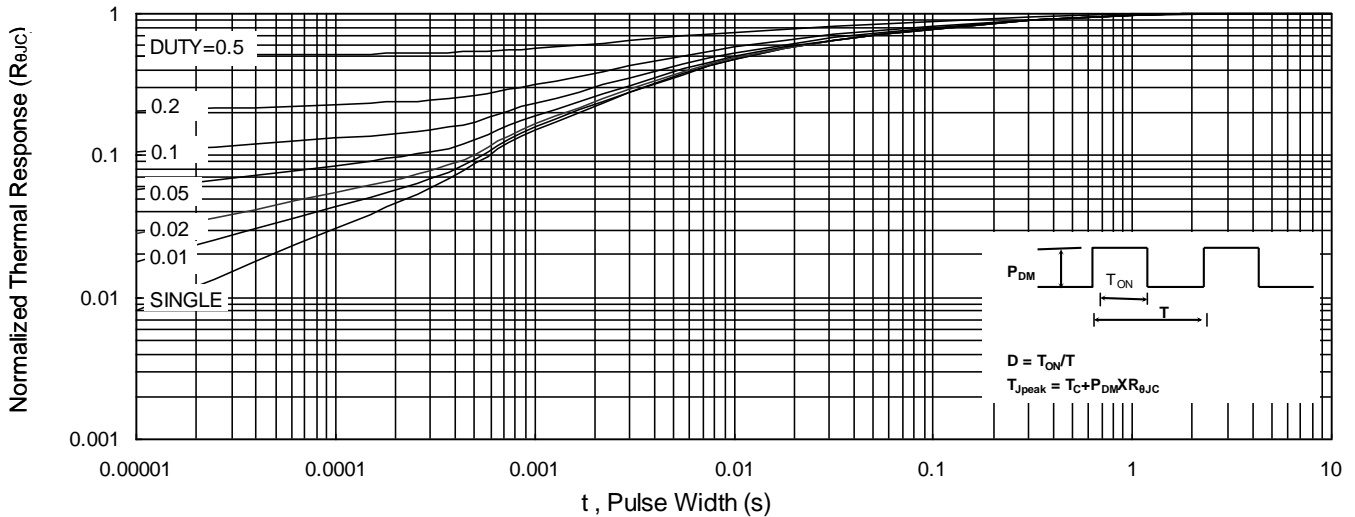


Fig.9 Normalized Maximum Transient Thermal Impedance

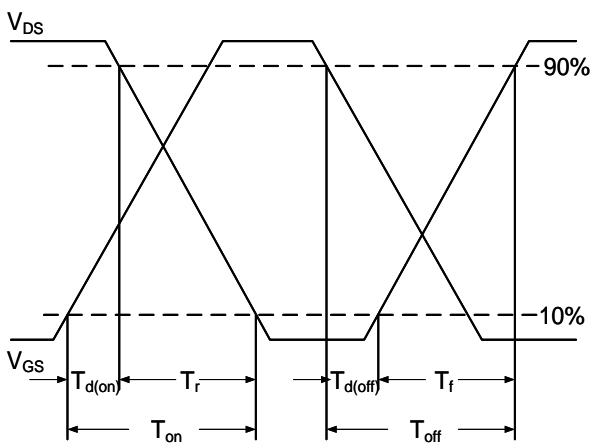


Fig.10 Switching Time Waveform

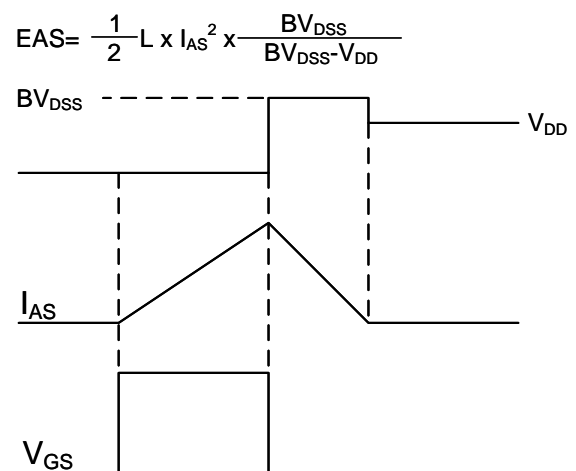


Fig.11 Unclamped Inductive Switching Waveform



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